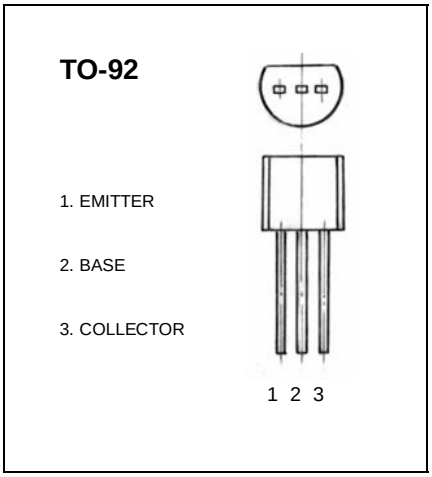
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

KSA539 TRANSISTOR (PNP)



FEATURES

Power dissipation

$P_{CM:}$ 0.4 W (Tamb=25℃)

Collector current

$I_{CM:}$ -0.2 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic=- 100μA , I_E=0	-60			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= -10 mA, I_B=0	-45			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=-10μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -45V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -3V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}= -1V, I_C= -50mA	40		240	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-150mA, I_B=-15 mA			-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-150mA, I_B=-15 mA			-1.2	V

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	120-240